

MOSFET, Power; Dual N-Ch; VDSS 20V; RDS(ON) 0.023Ω; ID 6.6A; SO-8; PD 2W; VGS +/-12V

Manufacturers	<u>Infinion Technologies Corporation</u>
Package/Case	SOIC-8
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRF7311TRPBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

- Generation V Technology
- Ultra Low On-Resistance
- Dual N-Channel MOSFET
- Surface Mount
- Fully Avalanche Rated

Features

RoHS Compliant

Low RDS(on)

Dynamic dv/dt Rating

Fast Switching

Dual N-Channel MOSFET

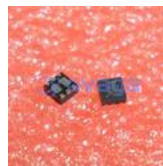


Related Products



[IRLTS6342TRPBF](#)

Infineon Technologies Corporation
TSOP-6



[IRLHS6376TRPBF](#)

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PQFN2x2DD



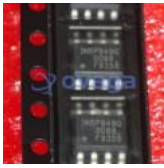
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